

PTO-1449

ATTORNEY'S DKT NO.
025219-268

APPLICATION NO.
09/600,590

APPLICANT
Bernard Aspar, et al.

FILING DATE
July 19, 2000

GROUP
Unassigned

U.S. PATENT DOCUMENTS

| EXAMINER'S INITIALS | PATENT NO. | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
|---------------------|------------|------|------|-------|----------|-------------|
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FOREIGN PATENT DOCUMENTS

| EXAMINER'S INITIALS | PATENT NO. | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
|---------------------|------------|-----------|---------|-------|----------|-------------|----|
| | | | | | | Yes | No |
| KIK | FR 2861472 | Mar. 1993 | FR | | | / | |
| KIK | EP 0412002 | Feb. 1991 | EP | | | / | |
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RECEIVED
AUG 31 2000
TOLSON MAIL ROOM

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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| 111 | Y.H. Lo "New approach to grow pseudomorphic structures over the critical thickness", <i>1991 American Institute of Physics, pp.2311-2313.</i> |
| 111 | J.F. Klem, et al. "Characterization of thin AlGaAs/InGaAs/GaAs quantum-well structures bonded directly to SiO ₂ /Si and glass substrates", <i>1989 American Institute of Physics, pp.459-462.</i> |
| 111 | F.E. Ejeckam, et al. "Dislocation-free InSb grown on GaAs compliant universal substrates", <i>1997 American Institute of Physics, pp. 776-778.</i> |
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| EXAMINER | DATE CONSIDERED |
| JK RK | 10-18-02 |

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.